

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

5 **Listing of Claims:**

1. (currently amended) An optical proximity correction (OPC) method for correcting a photomask layout, wherein the photomask layout comprises at least a photomask pattern, the OPC method comprising:

10 collecting an assist feature bias of a predetermined first assist feature which will be added to the photomask layout;

performing a rule-based OPC process by taking account of the assist feature bias to compute a target bias of the photomask layout and output a corrected photomask layout according to the target bias; and

15 adding the predetermined first assist feature to the corrected photomask layout.

2. (currently amended) The OPC method of claim 1, wherein the predetermined first assist feature is a scattering bar.

20 3. (original) The OPC method of claim 1, further comprising using the collected assist feature bias to build an assist feature correction model for the rule-based OPC process.

4. (original) The OPC method of claim 1, further comprising transferring the collected assist feature bias to a specific format for the ruled-based OPC process.

25 5. (original) The OPC method of claim 1, wherein the rule-based OPC process is used for correcting an edge portion of the photomask pattern.

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6. (original) The OPC method of claim 1, wherein the rule-based OPC process comprises:

collecting a width and a spacing of the photomask pattern to obtain a parameter of the photomask pattern; and

5 adding a second assist feature using a correction rule of a database according to the parameter of the photomask pattern.

7. (original) The OPC method of claim 6, wherein the second assist feature is a serif or a hammerhead pattern.

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